

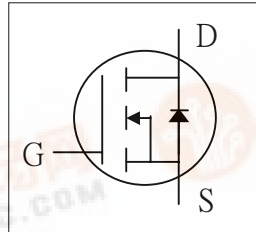
# AP03N70F



**Advanced Power Electronics Corp.**

*N-CHANNEL ENHANCEMENT MODE  
POWER MOSFET*

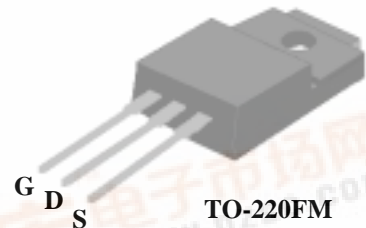
- ▼ Dynamic dv/dt Rating
- ▼ Repetitive Avalanche Rated
- ▼ Fast Switching
- ▼ Simple Drive Requirement



$BV_{DSS}$	600/650/700V
$R_{DS(ON)}$	3.6Ω
$I_D$	3.3A

## Description

AP03N70 series are specially designed as main switching devices for universal 90~265VAC off-line AC/DC converter applications. TO-220FM type provide high blocking voltage to overcome voltage surge and sag in the toughest power system with the best combination of fast switching, ruggedized design and cost-effectiveness.



The TO-220FM package is universally preferred for all commercial-industrial applications. The device is suited for switch mode power supplies, DC-AC converters and high current high speed switching circuits.

## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage - /A/H	600/650/700	V
$V_{GS}$	Gate-Source Voltage	± 30	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS}$ @ 10V	3.3	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS}$ @ 10V	2.1	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	13.2	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	29	W
	Linear Derating Factor	0.23	W/°C
$E_{AS}$	Single Pulse Avalanche Energy <sup>2</sup>	85	mJ
$I_{AR}$	Avalanche Current	3.3	A
$E_{AR}$	Repetitive Avalanche Energy	3.3	mJ
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Thermal Resistance Junction-case Max.	4.3	°C/W
Rthj-a	Thermal Resistance Junction-ambient Max.	62	°C/W





**Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =1mA / -	600	-	-	V
		V <sub>GS</sub> =0V, I <sub>D</sub> =1mA / A	650	-	-	V
		V <sub>GS</sub> =0V, I <sub>D</sub> =1mA / H	700	-	-	V
ΔBV <sub>DSS</sub> /ΔT <sub>j</sub>	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =1mA	-	0.6	-	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =1.6A	-	-	3.6	Ω
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	2	-	4	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =1.6A	-	2	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current (T <sub>j</sub> =25°C)	V <sub>DS</sub> =600V, V <sub>GS</sub> =0V	-	-	10	uA
	Drain-Source Leakage Current (T <sub>j</sub> =150°C)	V <sub>DS</sub> =480V, V <sub>GS</sub> =0V	-	-	100	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> = ± 30V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>3</sup>	I <sub>D</sub> =3.3A	-	11.4	-	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =480V	-	3.1	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =10V	-	4.2	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>3</sup>	V <sub>DD</sub> =300V	-	8.4	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =3.3A	-	6	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =10Ω, V <sub>GS</sub> =10V	-	17.7	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =91Ω	-	5.9	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	600	-	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V	-	45	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	4	-	pF

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I <sub>S</sub>	Continuous Source Current ( Body Diode )	V <sub>D</sub> =V <sub>G</sub> =0V , V <sub>S</sub> =1.5V	-	-	3.3	A
I <sub>SM</sub>	Pulsed Source Current ( Body Diode ) <sup>1</sup>		-	-	13.2	A
V <sub>SD</sub>	Forward On Voltage <sup>3</sup>	T <sub>j</sub> =25°C, I <sub>S</sub> =3.3A, V <sub>GS</sub> =0V	-	-	1.5	V

**Notes:**

- 1.Pulse width limited by safe operating area.
- 2.Starting T<sub>j</sub>=25°C , V<sub>DD</sub>=50V , L=15mH , R<sub>G</sub>=25Ω , I<sub>AS</sub>=3.3A.
- 3.Pulse width ≤300us , duty cycle ≤2%.

**Ordering Code**

AP03N70F- X : X Denote BV<sub>DSS</sub> Grade

Blank = BV<sub>DSS</sub> 600V

A = BV<sub>DSS</sub> 650V

H = BV<sub>DSS</sub> 700V

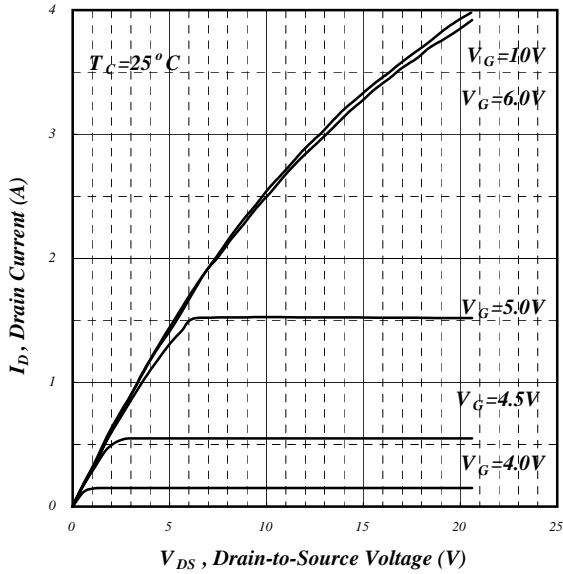


Fig 1. Typical Output Characteristics

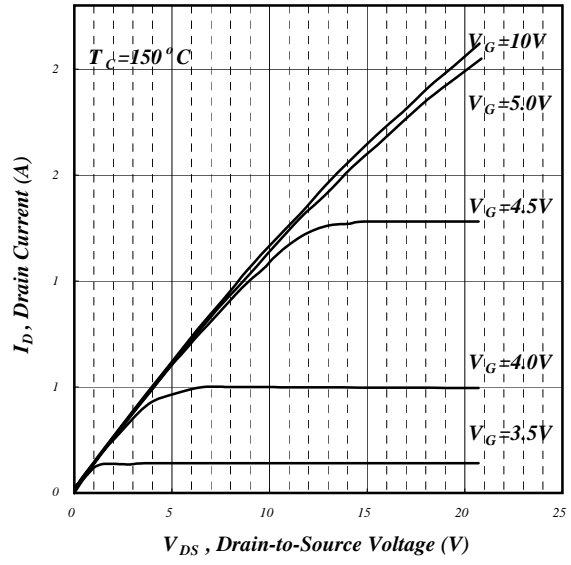


Fig 2. Typical Output Characteristics

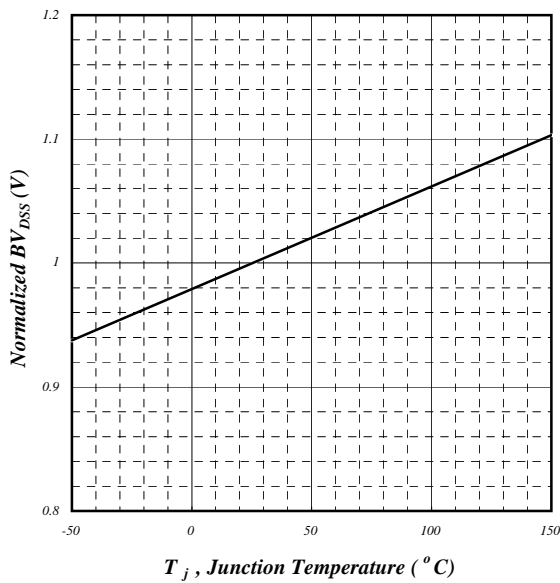


Fig 3. Normalized  $BV_{DSS}$  v.s. Junction Temperature

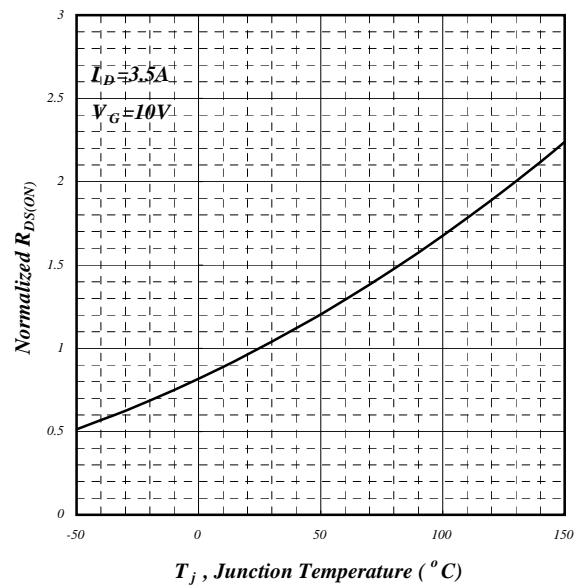


Fig 4. Normalized On-Resistance v.s. Junction Temperature

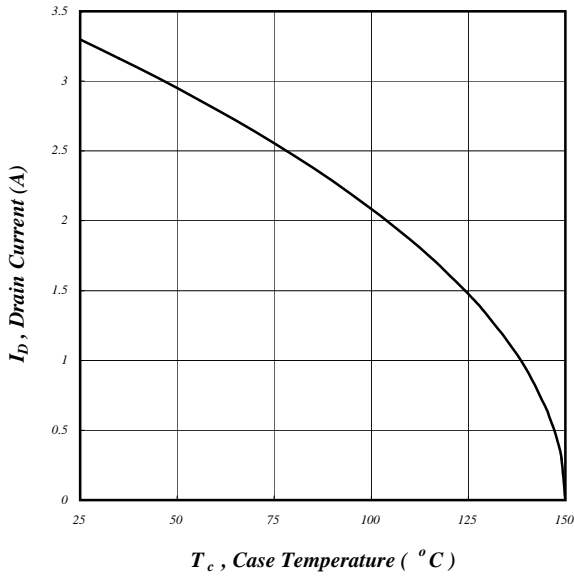


Fig 5. Maximum Drain Current v.s. Case Temperature

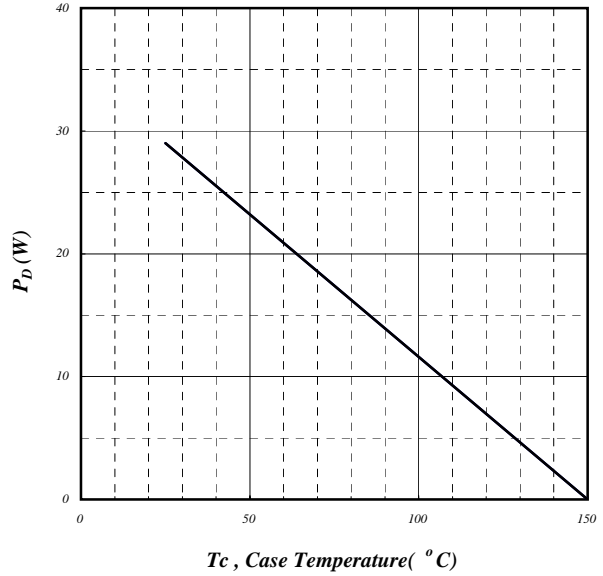


Fig 6. Typical Power Dissipation

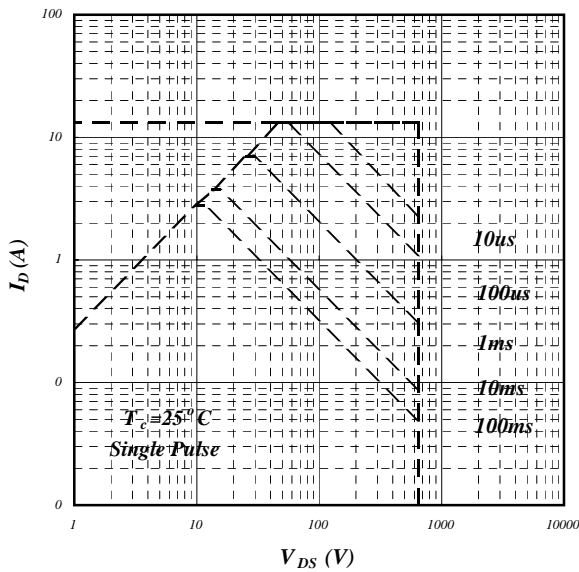


Fig 7. Maximum Safe Operating Area

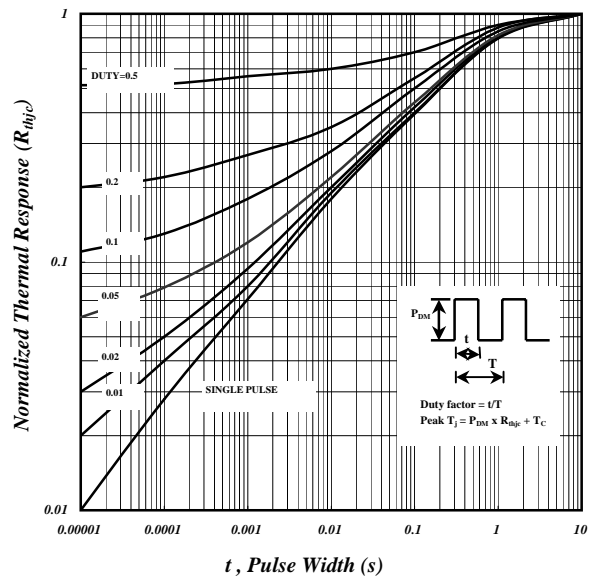


Fig 8. Effective Transient Thermal Impedance

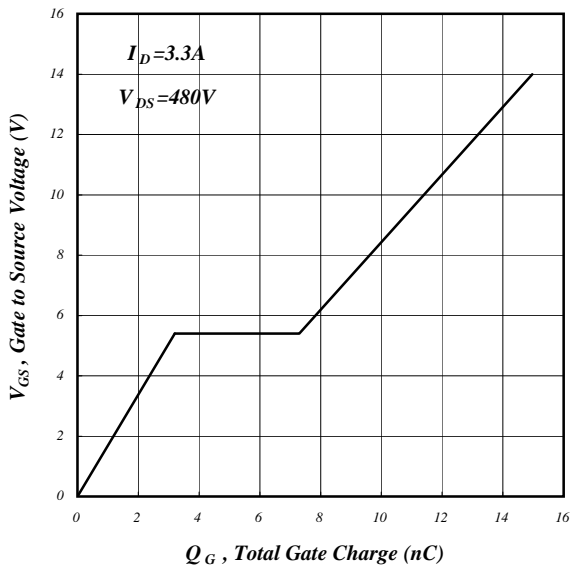


Fig 9. Gate Charge Characteristics

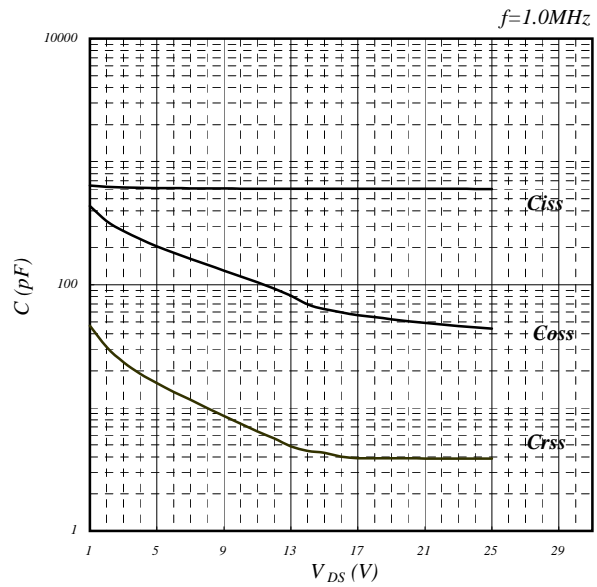


Fig 10. Typical Capacitance Characteristics

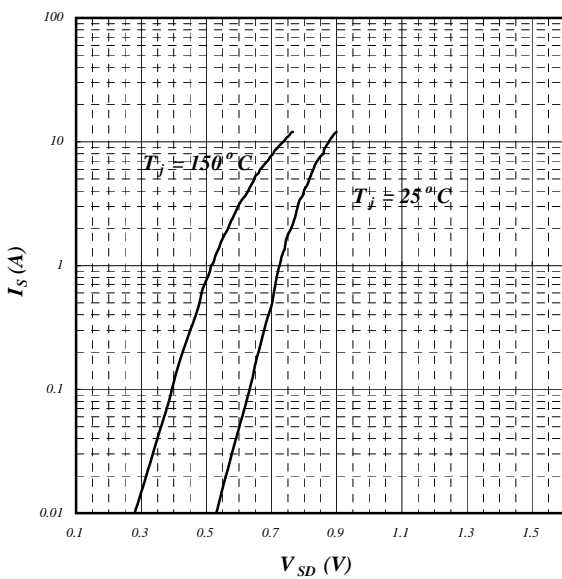


Fig 11. Forward Characteristic of Reverse Diode

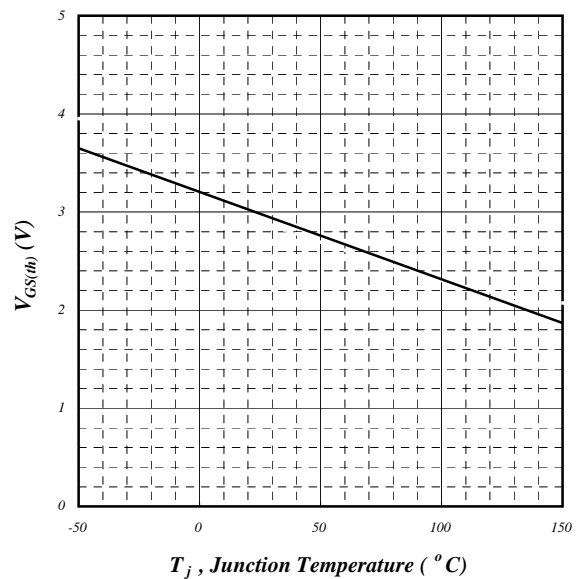


Fig 12. Gate Threshold Voltage v.s. Junction Temperature

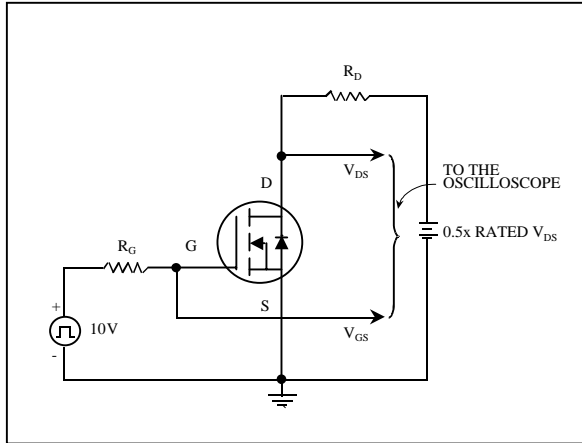


Fig 13. Switching Time Circuit

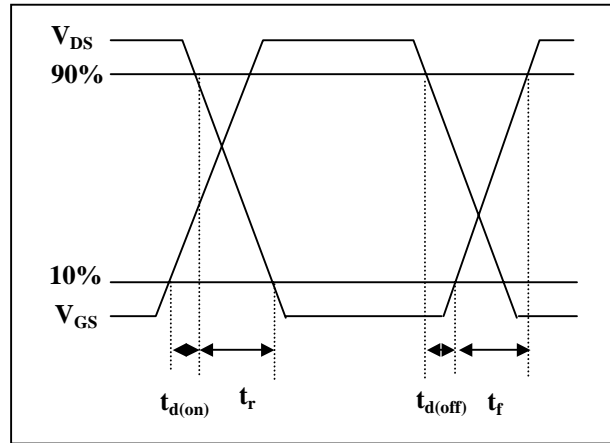


Fig 14. Switching Time Waveform

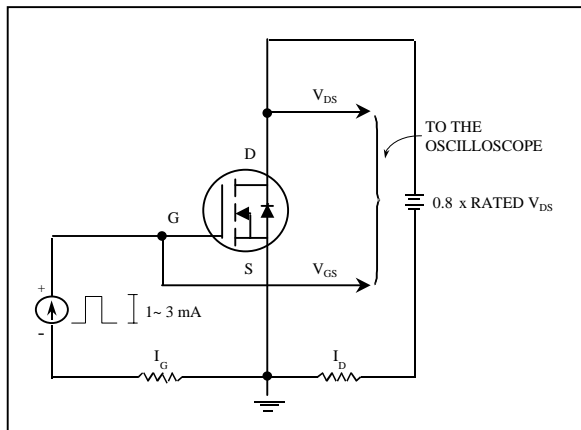


Fig 15. Gate Charge Circuit

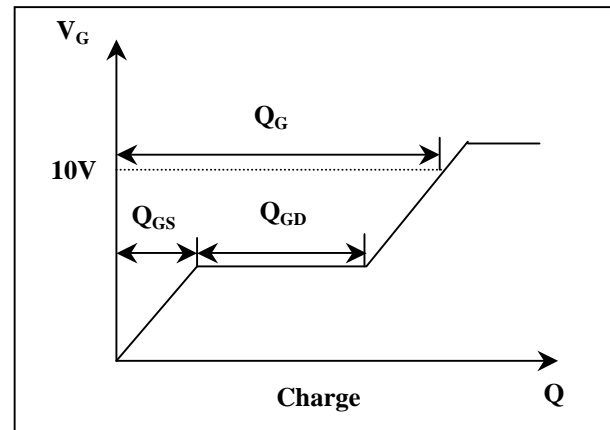


Fig 16. Gate Charge Waveform